## A-4 Plasma Applications

### **Representative Organizer**

Kenji ISHIKAWA (Nagoya University)

### **Co-organizers**

Koji ERIGUCHI (Kyoto University)

Kenji MAEDA (Hitachi, Ltd.)

Masanaga FUKASAWA (Sony Corporation)

Taisei MOTOMURA (National Institute of Advanced Industrial Science and Technology)

## Oral Session 1 March 27 (Fri.) Room 1

Chair: Kenji Ishikawa (Nagoya University)

# 15:30 A4-I-01 Electron Energy Distribution Control in Plasma Etchers: Breaking from the Conventional Flux Ratio Scaling Rules in Etch for Precise Passivation Control [Invited Lecture]

<sup>1</sup><u>Alok Ranjan</u>, <sup>1</sup>Mingmei Wang, <sup>2</sup>Peter Ventzek 1 TEL TECHNOLOGY CENTER, AMERICA, LLC 2 TOKYO ELECTRON AMERICA, INC.

## 16:00 A4-O-01 Challenges of Contact Etching for 14 nm FDSOI Technology

<sup>1</sup>Mokrane Mebarki, <sup>2</sup>Maxime Darnon, <sup>1</sup>Cécile Jenny, <sup>1</sup>Delia Ristoiu, <sup>3</sup>Nicolas Posseme, <sup>2</sup>Oliver Joubert 1 STMICROELECTRONICS 2 LTM-CNRS 3 CEA-LETI

## 16:15 A4-O-02 Tight-Binding Quantum Chemical Molecular Dynamics Simulation for the Elucidation of SiC Etching Mechanism

<u>Hiroshi Ito</u>, Takuya Kuwahara, Yuji Higuchi, Nobuki Ozawa, Momoji Kubo GRADUATE SCHOOL OF ENGINEERING, TOHOKU UNIVERSITY

## 16:30 A4-O-03 Effect of Microwave Plasma Treatment of Sumiconductor Emitter Surface on Photon Enhanced Thermionic Emission

<sup>1</sup><u>Akihisa Ogino</u>, <sup>1</sup>Kengo Inoue, <sup>1</sup>Kazuhiro Shirakura, <sup>1</sup>Atsushi Hada, <sup>2</sup>Kenjiro Murata, <sup>2</sup>Takatoshi Watanabe 1 GRADUATE SCHOOL OF ENGINEERING, SHIZUOKA UNIVERSITY 2 FACULTY OF ENGINEERING, SHIZUOKA UNIVERSITY

## Oral Session 2 March 28 (Sat.) Room 1

Chair: Akihisa Ogino (Shizuoka University)

# 13:30 A4-I-02 Advanced Plasma Processing for Controlled Synthesis of Atomically-Thin Semiconductor Nanomaterials [Invited Lecture]

Toshiaki Kato, Toshiro Kaneko

DEPARTMENT OF ELECTRONIC ENGINEERING, TOHOKU UNIVERSITY

## 14:00 A4-O-04 Investigation of Annealing-Induced Recovery Behavior of Graphenes Doped by Ammonia Plasma

Byeong-Joo Lee, Goo-Hwan Jeong

DEPARTMENT OF NANO APPLIED ENGINEERING, KANGWON NATIONAL UNIVERSITY

# 14:15 A4-O-05 Influence of Applied Voltage Waveforms in Surface Dielectric Barrier Discharge on the Decomposition of Naphthalene

<sup>1</sup><u>Ayman Abdelfadeel Abdelaziz</u>, <sup>2</sup>Takafumi Seto, <sup>1</sup>Tatsuo Ishijima, <sup>2</sup>Yoshio Otani 1 RESEARCH CENTER FOR SUSTAINABLE ENERGY AND TECHNOLOGY, KANAZAWA UNIVERSITY 2 SCHOOL OF NATURAL SCIENCE, KANAZAWA UNIVERSITY

### 14:30 A4-O-06 Crednerite-CuMnO<sub>2</sub> Thin Films Prepared Using Atmospheric Pressure Plasma Annealing

Hong-Ying Chen, Yu-Chang Lin

DEPARTMENT OF CHEMICAL ANDMATERIALS ENGINEERING, NATIONAL KAOHSIUNG UNIVERSITY OF APPLIED

#### March 29 (Sun.) Oral Session 3 Room 1

Chair: Alok Ranjan (TEL Technology Center, America, LLC)

#### 8:50 A4-I-03 Plasma-Assisted Polishing for Damage-Free Atomically Flat Finishing of Wide Gap Semiconductor Materials [Invited Lecture]

K. Yamamura, H.Deng, K.Endo

RESEARCH CENTER FOR ULTRA-PRECISION SCIENCE AND TECHNOLOGY, OSAKA UNIVERSITY

#### 9:20 A4-O-07 Effect of SiH<sub>4</sub> Inductively Coupled Plasma Surface Treatment on Low Temperature and Low Resistance Ohmic Contact for AlGaN/GaN-Based Power Device

Xu Li, Konstantinos Floros, Gary Ternent, Abdullah Al-Khalidi, Edward Wasige, Iain G. Thayne SCHOOL OF ENGINEERING, UNIVERSITY OF GLASGOW

### 9:35 A4-O-08 The Effect of Ion Bombardment from BCl<sub>3</sub> Inductively Coupled Plasma on Resistivity of Ohmic Contact Formed on GaN-Based Epitaxial Structure

<sup>1</sup>Anton Kobeley, <sup>2</sup>Nickolai Andrianov, <sup>3</sup>Yuri Barsukov, <sup>1</sup>Alexander Smirnov

1 DEPARTMENT OF PLASMA PHYSICS, ST. PETERSBURG STATE POLYTECHNICAL UNIVERSITY

2 SVETLANA-ROST JSC

3 CODDAN TECHNOLOGIES LLC

Chair: Hajime Sakakita (AIST Tsukuba)

#### 9:50 A4-O-09 Inactivation of *P. digitatum* Spore on *Citrus Unshiu* by APDBD for Agricultural Applications of Plasma Technologies

<sup>1</sup>Yoshihito Yagyu, <sup>1</sup>Naokoi Matsumoto, <sup>1</sup>Yuta Hatayama, <sup>2</sup>Nobuya Hayashi, <sup>3</sup>Tomoko Mishima, <sup>3</sup>Terumi Nishioka, <sup>4</sup>Akikazu Sakudo, <sup>1</sup>Hiroharu Kawasaki, <sup>1</sup>Tamiko Ohshima, <sup>1</sup>Takeshi Ihara, <sup>1</sup>Yoshiaki Suda 1 DEP, OF ELECTRICAL AND ELECTRIC ENGINEERING, NATIONAL INSTITUTE OF TECH., SASEBO COLLEGE 2 FACULTY OF ENGINEERING SCIENCES, KYUSHU UNIVERSITY

3 RESEARCH INSTITUTE OF ENVIRONMENT, AGRICULTURE AND FISHERIES, OSAKA PREFECTURAL GOVERNMENT 4 FACULTY OF MEDICINE, UNIVERSITY OF THE RYUKYUS

### 10:05 A4-O-10 Quatitative Estimation of Inactivation of Fungal Spores Using an Atmospheric-Pressure Oxvgen-Radical Source

<sup>1</sup>Hiroshi Hashizume, <sup>2</sup>Keisuke Nishida, <sup>2</sup>Takayuki Ohta, <sup>1</sup>Masaru Hori, <sup>2</sup>Masafumi Ito

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